NSN 5961-00-415-2017

Semiconductor Device Set - Page 1 of 2

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Inclosure Material:

Metal all transistor

Overall Length:

1.003 inches all transistor

Overall Height:

0.330 inches all transistor

Overall Width:

0.505 inches all transistor

Mounting Facility Quantity:

2 all transistor

Internal Configuration:

Junction contact all transistor

Electrode Internally-electrically Connected To Case:

Collector all transistor

Internal Junction Configuration:

Npn all transistor

Component Function Relationship:

Matched

Component Name And Quantity:

2 transistor

Mounting Method:

Unthreaded hole all transistor

Semiconductor Material:

Silicon all transistor

Voltage Rating In Volts Per Characteristic:

300.0 breakdown voltage, collector-to-base, emitter open all transistor and 300.0 breakdown voltage, collector-to-emitter, with specified resistance between base and emitter all transistor and 5.0 breakdown voltage, emitter-to-base, collector open all transistor

Current Rating Per Characteristic:

3.00 microamperes zero-gate-voltage source current preset all transistor

Power Rating Per Characteristic:

5.0 watts small-signal input power, common-collector preset all transistor

Maximum Operating Tempurature Per Measurement Point:

200.0 degrees celsius junction all transistor

Precious Material And Location:

Terminal surfaces gold

Precious Material:

Gold

Test Data Document:

00752-334761 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing)

Terminal Type And Quantity:

3 uninsulated wire lead all transistor and 1 case all transistor

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

No

Fiig:

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